TOSHIBA Transistor Silicon NPN Triple Diffused Type

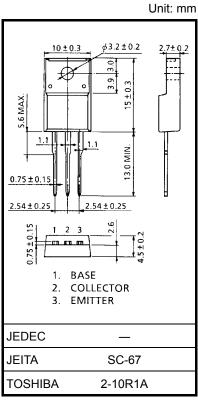
2SD2204

High-Power Switching Applications
Hammer Drive, Pulse Motor Drive Applications

- High DC current gain: $h_{FE} = 2000$ (min) ($V_{CE} = 3$ V, $I_{C} = 1.5$ A)
- Low saturation voltage: $V_{CE (sat)} = 1.5 \text{ V (max) (IC} = 1.5 \text{ A)}$

Absolute Maximum Ratings (Tc = 25°C)

| Characteristics | | Symbol | Rating | Unit | |
|-----------------------------|-----------|------------------|------------|------|--|
| Collector-base voltage | | V_{CBO} | 65 ± 10 | V | |
| Collector-emitter voltage | | V _{CEO} | 65 ± 10 | V | |
| Emitter-base voltage | | V _{EBO} | 7 | V | |
| Collector current | DC | I _C | 4 | Α | |
| | Pulse | I _{CP} | 6 | | |
| Base current | | Ι _Β | 0.5 | Α | |
| Collector power dissipation | Ta = 25°C | D. | 2.0 | W | |
| | Tc = 25°C | - P _C | 25 | | |
| Junction temperature | | Tj | 150 | °C | |
| Storage temperature range | | T _{stg} | -55 to 150 | °C | |



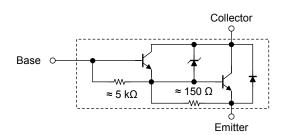
Weight: 1.7 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high

temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Equivalent Circuit

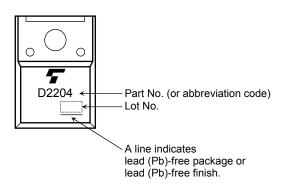


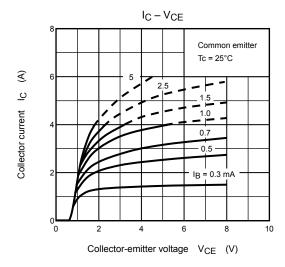
Electrical Characteristics (Tc = 25°C)

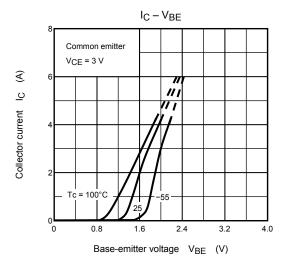
| Chara | acteristics | Symbol | Test Condition | Min | Тур. | Max | Unit | |
|--------------------------------------|-------------------|---------------------------|---|--------------------------------------|------|-------|------|--|
| Collector cut-off of | current | I _{CBO} | V _{CB} = 45 V, I _E = 0 | _ | _ | 100 | μΑ | |
| Emitter cut-off cu | rrent | I _{EBO} | V _{EB} = 6 V, I _C = 0 | _ | _ | 2.5 | mA | |
| Collector-emitter | breakdown voltage | V (BR) CEO | I _C = 10 mA, I _B = 0 | 55 | 65 | 75 | V | |
| DC current gain | | h _{FE (1)} | V _{CE} = 3 V, I _C = 1.5 A | = 3 V, I _C = 1.5 A 2000 — | | 15000 | | |
| | | h _{FE (2)} | V _{CE} = 3 V, I _C = 3 A | 1000 | _ | _ | | |
| Collector-emitter saturation voltage | | V _{CE} (sat) (1) | I _C = 1.5 A, I _B = 3 mA | _ | _ | 1.5 | V | |
| | | V _{CE} (sat) (2) | I _C = 3 A, I _B = 12 mA | _ | _ | 2.0 | V | |
| Base-emitter saturation voltage | | V _{BE} (sat) | I _C = 1.5 A, I _B = 3 mA | _ | _ | 2.0 | V | |
| Switching time | Turn-on time | t _{on} | Output Input $B1$ $B1$ C C C C C C C | _ | 1.0 | _ | μѕ | |
| | Storage time | t _{stg} | | _ | 5.0 | _ | | |
| | Fall time | t _f | | _ | 2.0 | _ | | |

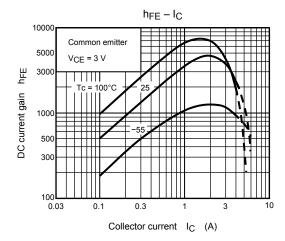
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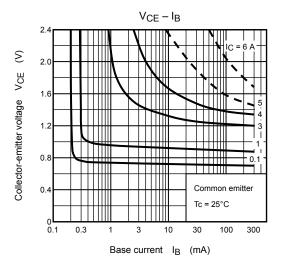
Marking

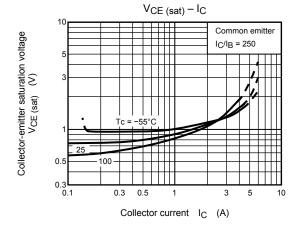


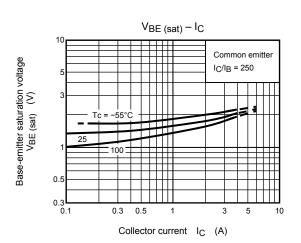


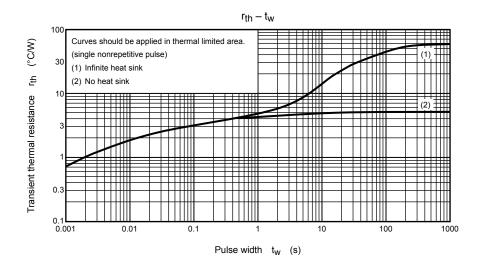


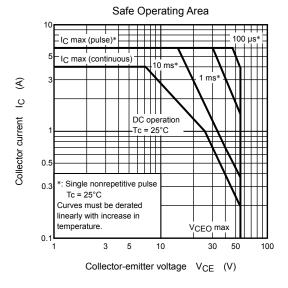


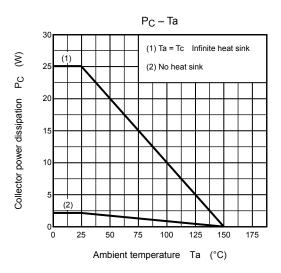












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